



TO-92L Plastic-Encapsulated Transistors

2SB562 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: \quad 900 \quad \text{mW (Tamb=25°C)}$$

Collector current

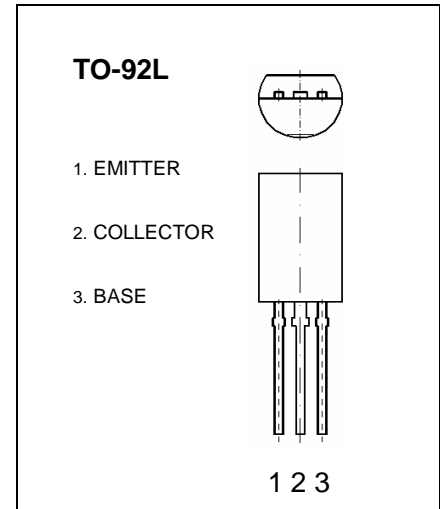
$$I_{CM}: \quad -1 \quad \text{A}$$

Collector-base voltage

$$V_{(BR)CBO}: \quad -25 \quad \text{V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: \quad -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20\text{V}, I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -2\text{V}, I_C = -0.5\text{A}$	85		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -0.8\text{A}, I_B = -0.08\text{A}$			-0.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = -2\text{V}, I_C = -0.5\text{A}$			-1	V
Transition frequency	f_T	$V_{CE} = -2\text{V}, I_C = -0.5\text{A}$		350		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		38		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C
Range	85-170	120-240